



P A T E N T

Attorney Docket No.
33035 M 0341

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:)
Kensaku MOTOKI, et al.) **CONFIRMATION NO.: 6887**
U.S. Serial No.: 10/691,540) Group Art Unit: 1722
Filed: October 24, 2003) Examiner: Matthew J. Song

For: **GaN SINGLE CRYSTAL SUBSTRATE AND METHOD OF MAKING THE SAME**

**INFORMATION DISCLOSURE STATEMENT AS SUBMISSION
IN REQUEST FOR CONTINUED EXAMINATION**

MAIL STOP: ISSUE FEE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The Issue and Publication Fees for this application are due on October 2, 2007. In lieu of the Fees, this Information Disclosure Statement (IDS) and Citation Form (PTO-1449) are submitted with a Request for Continued Examination (RCE). This IDS is being filed to submit five (5) additional documents to the USPTO, which documents were cited in a prior Japanese Patent Office (JPO) action.

It is respectfully requested that the cited documents be considered by the Examiner in the above-identified patent application and that the cited documents be made officially of record

U. S. Patent Application No. 10/691,540
Attorney Docket No. 033035 M 0341
Page 2

therein. It is further requested that a listing of the same appear on the face of any patent which may issue from this application.

Respectfully submitted,
SMITH, GAMBRELL & RUSSELL, LLP

By: 

Michael A. Makuch, Reg. No. 32,263
1850 M Street, N.W., Suite 800
Washington, D.C. 20036
Telephone: (202)263-4300
Facsimile: (202) 263-4329

Dated: August 29, 2007



FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET 033035 M 0341	SERIAL NO. 10/691,540
	APPLICANTS: Kensaku MOTOKI, et al.	
	FILING DATE October 24, 2003	GROUP ART UNIT 1722

U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLAS S	ABSTRACT TRANSLATION YES NO
	AH	97/11518	03/27/97	WO			X
	AI	07-273048	10/20/1995	JP			X
	AJ	11-135770	05/21/1999	JP			X
	AK						

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

	AL	Japanese Patent Office Action for corresponding Patent Application No. 2000-519462 (April 18, 2006)
	AM	H. Okumura, et al. "Epitaxial growth of cubic and hexagonal GaN on GaAs on GaAs by gas-source molecular epitaxy," Appl. Phys. Lett. 59(9), 1991.08.26, pp. 1058-1060
	AN	NANIWAE, et al., "Growth of Single Crystal GaN Substrate Using Hydride Vapor Phase Epitaxy," Journal of Crystal Growth 99, 1990, pp. 381-384
	AO	
	AP	
	AQ	

EXAMINER:

DATE CONSIDERED:

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.